

Medium current, high performance, low voltage PNP transistor

Features

- Very low collector to emitter saturation voltage
- DC current gain, $h_{FE} > 100$
- 3 A continuous collector current
- 40 V breakdown voltage $V_{(BR)CER}$

Applications

- Power management in portable equipment
- Voltage regulation in bias supply circuits
- Switching regulator in battery charger applications
- Heavy load driver

Description

The device is manufactured in low voltage PNP planar technology by using a "Base Island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.

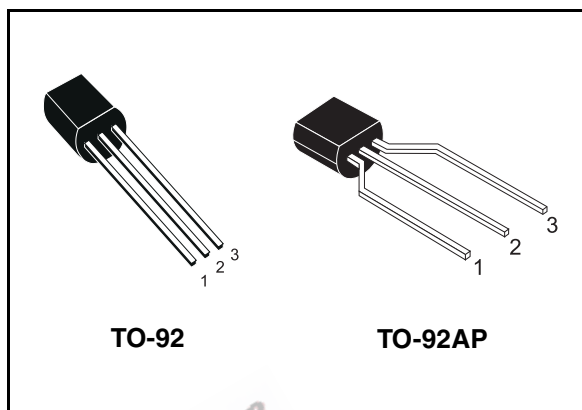


Figure 1. Internal schematic diagram

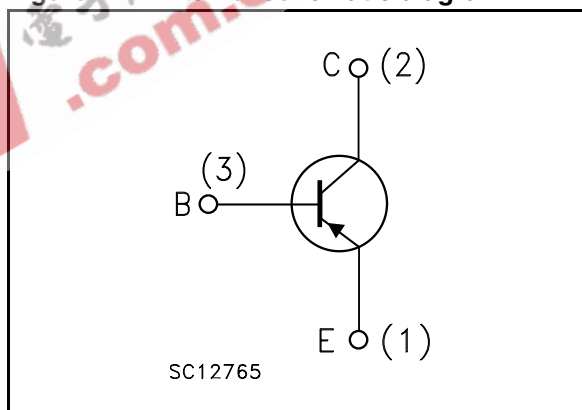


Table 1. Device summary

Order code	Marking	Package	Packaging
STX790A	X790A	TO-92	Bulk
STX790A-AP	X790A	TO-92 AP	Ammopack

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	-40	V
V_{CER}	Collector-emitter voltage ($R_{BE} = 47 \Omega$)	-40	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-30	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	-5	V
I_C	Collector current	-3	A
I_{CM}	Collector peak current ($t_p < 5$ ms)	-6	A
P_{tot}	Total dissipation at $T_{amb} = 25$ °C	0.9	W
T_{stg}	Storage temperature	-65 to 150	°C
T_J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	44.6	°C/W
$R_{thj-amb}$	Thermal resistance junction-amb max	139	°C/W

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_{\text{E}} = 0$)	$V_{\text{CB}} = -30\text{ V}$ $V_{\text{CB}} = -30\text{ V}; T_{\text{C}} = 100\text{ °C}$			-10 -100	μA μA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = -4\text{ V}$			-10	μA
$V_{(\text{BR})\text{CEO}}^{(1)}$	Collector-emitter breakdown voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = -10\text{ mA}$	-30			V
$V_{(\text{BR})\text{CER}}^{(1)}$	Collector-emitter breakdown voltage ($R_{\text{BE}} = 47\ \Omega$)	$I_{\text{C}} = -10\text{ mA}$	-40			V
$V_{(\text{BR})\text{CBO}}$	Collector-base breakdown voltage ($I_{\text{E}} = 0$)	$I_{\text{C}} = -100\ \mu\text{A}$	-40			V
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ($I_{\text{C}} = 0$)	$I_{\text{E}} = -100\ \mu\text{A}$	-5			V
$V_{\text{CE}(\text{sat})}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = -0.5\text{ A}$ $I_{\text{B}} = -5\text{ mA}$ $I_{\text{C}} = -1.2\text{ A}$ $I_{\text{B}} = -20\text{ mA}$ $I_{\text{C}} = -2\text{ A}$ $I_{\text{B}} = -20\text{ mA}$ $I_{\text{C}} = -3\text{ A}$ $I_{\text{B}} = -100\text{ mA}$ $I_{\text{C}} = -3\text{ A}$ $I_{\text{B}} = -100\text{ mA}$ $T_{\text{J}} = 100\text{ °C}$			-0.15 -0.25 -0.5 -0.7 -0.9	V V V V V
$V_{\text{BE}(\text{sat})}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = -1\text{ A}$ $I_{\text{B}} = -10\text{ mA}$		-0.8	-1	V
$V_{\text{BE}(\text{on})}^{(1)}$	Base-emitter on voltage	$I_{\text{C}} = -1\text{ A}$ $V_{\text{CE}} = -2\text{ V}$		-0.8	-1	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = -10\text{ mA}$ $V_{\text{CE}} = -2\text{ V}$ $I_{\text{C}} = -500\text{ mA}$ $V_{\text{CE}} = -2\text{ V}$ $I_{\text{C}} = -1\text{ A}$ $V_{\text{CE}} = -2\text{ V}$ $I_{\text{C}} = -2\text{ A}$ $V_{\text{CE}} = -1\text{ V}$ $I_{\text{C}} = -3\text{ A}$ $V_{\text{CE}} = -1\text{ V}$	100 100 100 100 90	200 200 160 130	400 400	

Table 4. Electrical characteristics (continued)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
f_t	Transition frequency	$I_C = -50 \text{ mA}$ $V_{CE} = -5 \text{ V}$ $f = 50 \text{ MHz}$		100		MHz
t_d	Resistive load Delay time	$I_C = -3 \text{ A}$ $V_{CC} = -20 \text{ V}$		180	220	ns
t_r	Rise time	$I_{B1} = -I_{B2} = -60 \text{ mA}$		160	210	ns
t_s	Storage time	see Figure 8		250	300	ns
t_f	Fall time			80	100	ns

1. Pulse duration = 300 μs , duty cycle $\leq 1.5\%$

2.1 Electrical characteristics (curves)

Figure 2. DC current gain

Figure 3. DC current gain

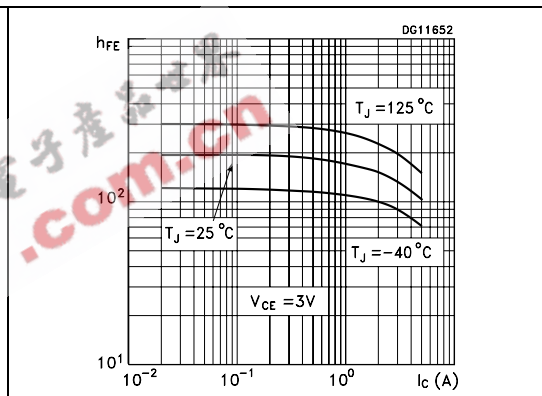
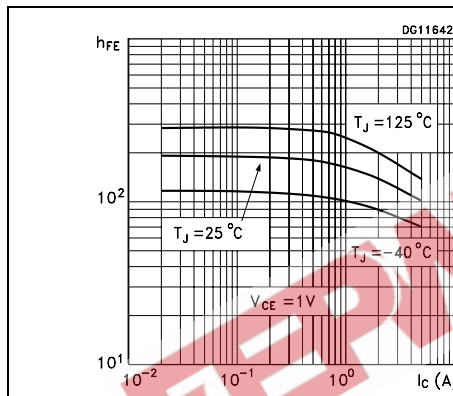


Figure 4. Collector-emitter saturation voltage

Figure 5. Base-emitter saturation voltage

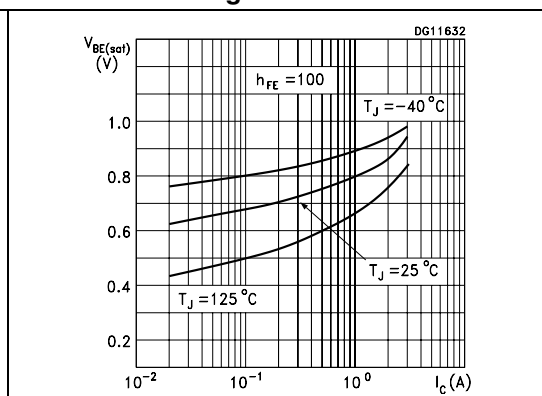
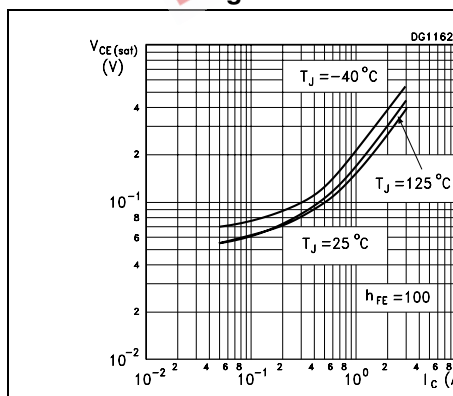
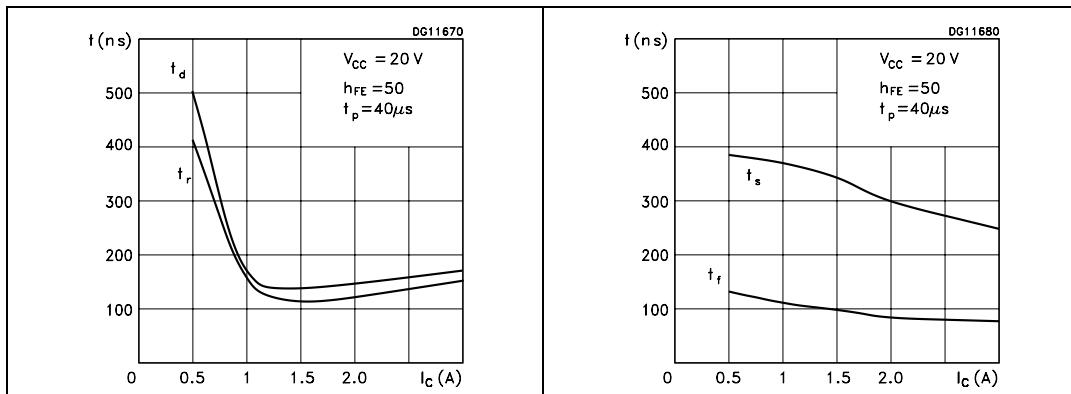
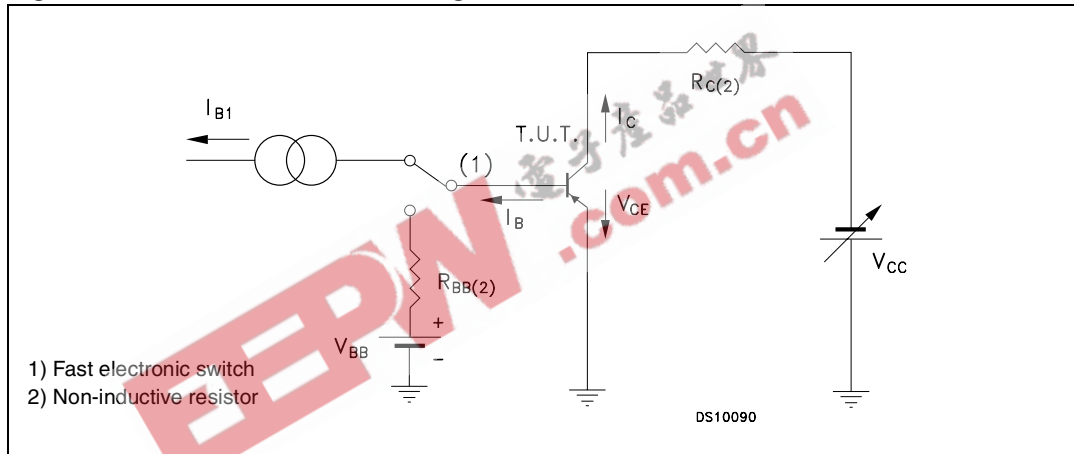


Figure 6. Switching time resistive load Figure 7. Switching time resistive load



2.2 Test circuit

Figure 8. Resistive load switching test circuit



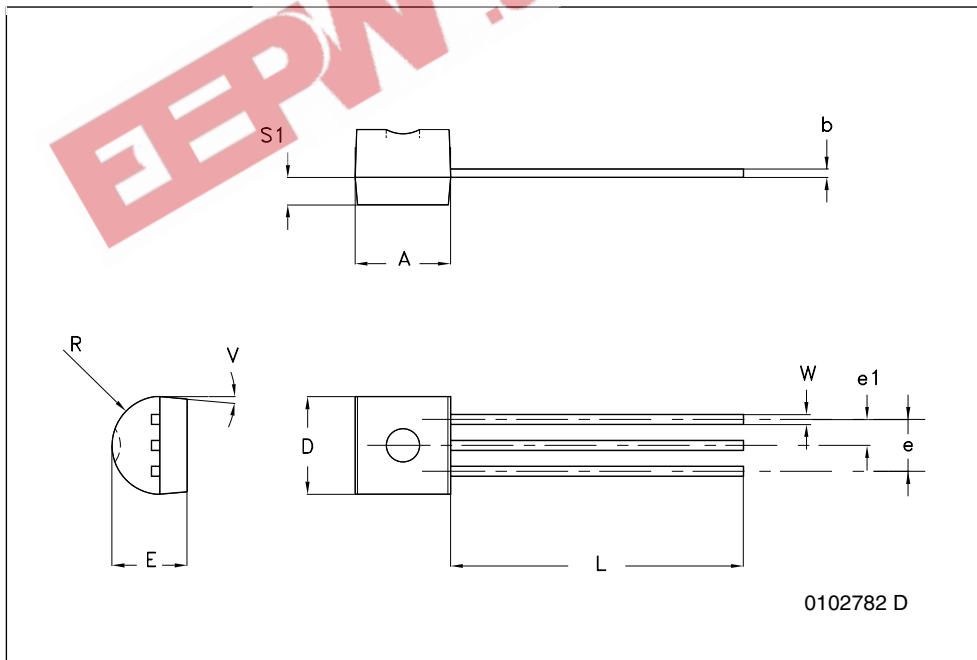
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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TO-92 bulk shipment mechanical data

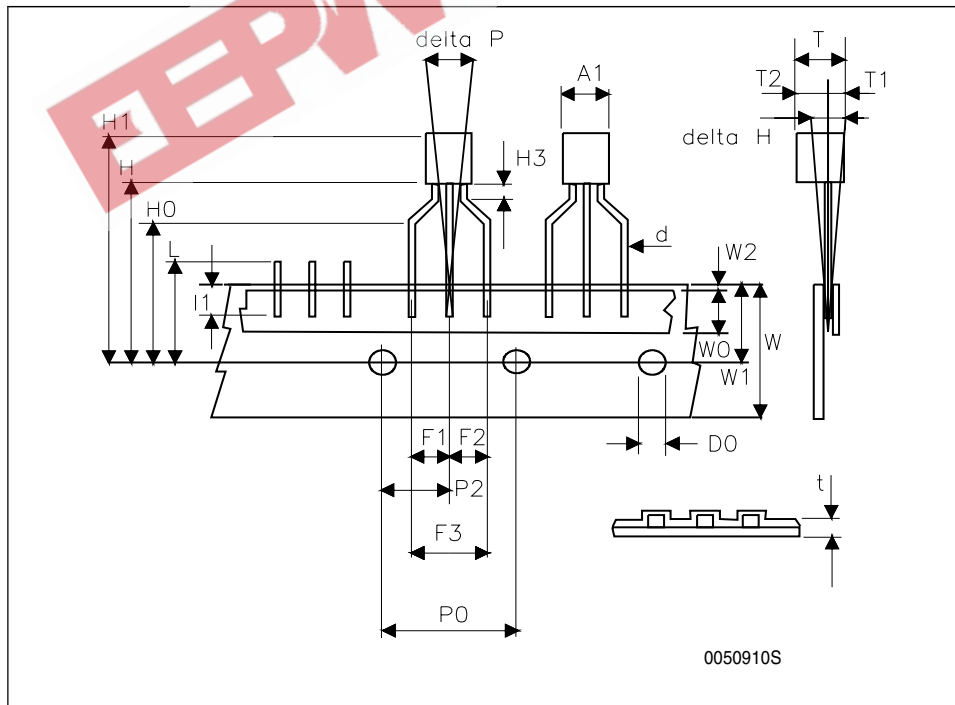
DIM.	mm.		
	MIN.	TYP	MAX.
A	4.32		4.95
b	0.36		0.51
D	4.45		4.95
E	3.30		3.94
e	2.41		2.67
e1	1.14		1.40
L	12.70		15.49
R	2.16		2.41
S1	0.92		1.52
W	0.41		0.56
V		5°	



0102782 D

TO-92 ammpack shipment (suffix"-AP") mechanical data

Dim.	mm		
	Min	Typ	Max
A1			4.80
T			3.80
T1			1.60
T2			2.30
d			0.48
P0	12.50	12.70	12.90
P2	5.65	6.35	7.05
F1,F2	2.44	2.54	2.94
F3	4.98	5.08	5.48
delta H	-2.00		2.00
W	17.50	18.00	19.00
W0	5.70	6.00	6.30
W1	8.50	9.00	9.25
W2			0.50
H	18.50		20.50
H3	0.5	1	1.5
H0	15.50	16.00	16.50
H1			25.00
D0	3.80	4.00	4.20
t			0.90
L			11.00
l1	3.00		
delta P	-1.00		1.00



4 Revision history

Table 5. Document revision history

Date	Revision	Changes
24-Mar-2003	1	Initial release.
29-Mar-2006	2	New template.
25-Jun-2008	3	Updated TO-92 mechanical data.

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